

CMOS logic

Note Title

06-08-2007

Static: leakage

- diode

- subthreshold conduction

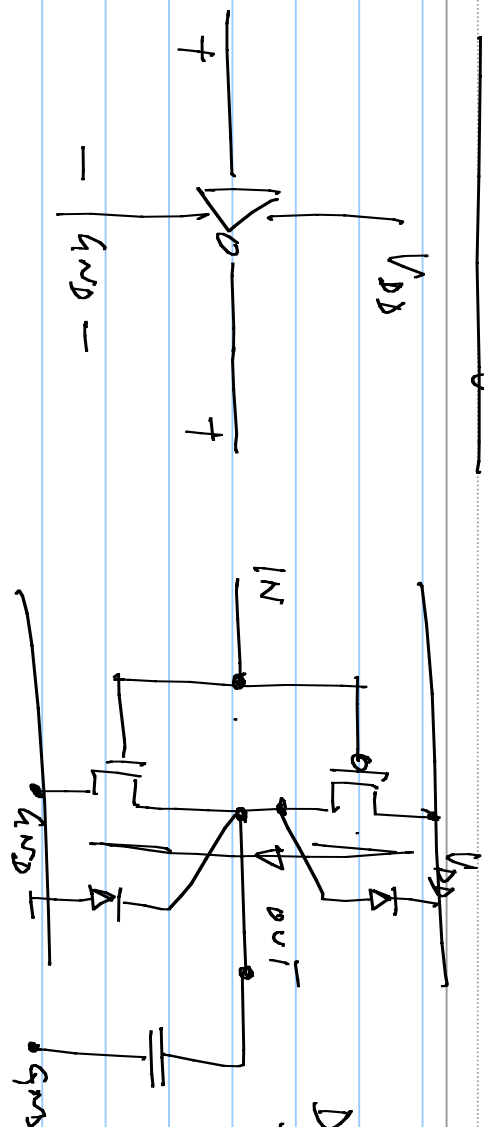
Dynamic power

- charging the load capacitor

crowbar current

- nMOS & pMOS on

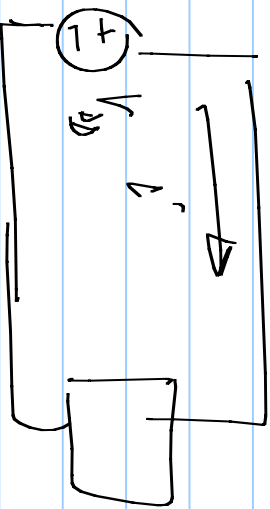
- Steeper signals at the input

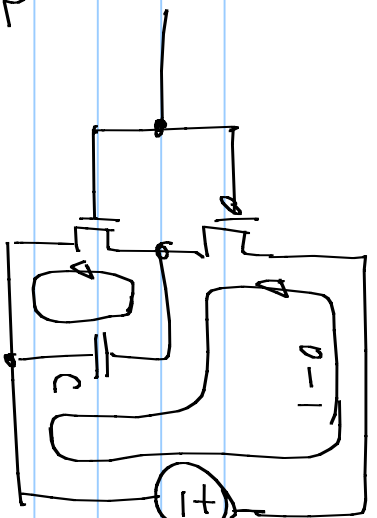


$$V_{TN} < V_{in} < V_{DD} - V_{TP}$$

$$P = C \cdot V_{DD}^2 \cdot f$$

≠ 0 → 1 transitions in a second



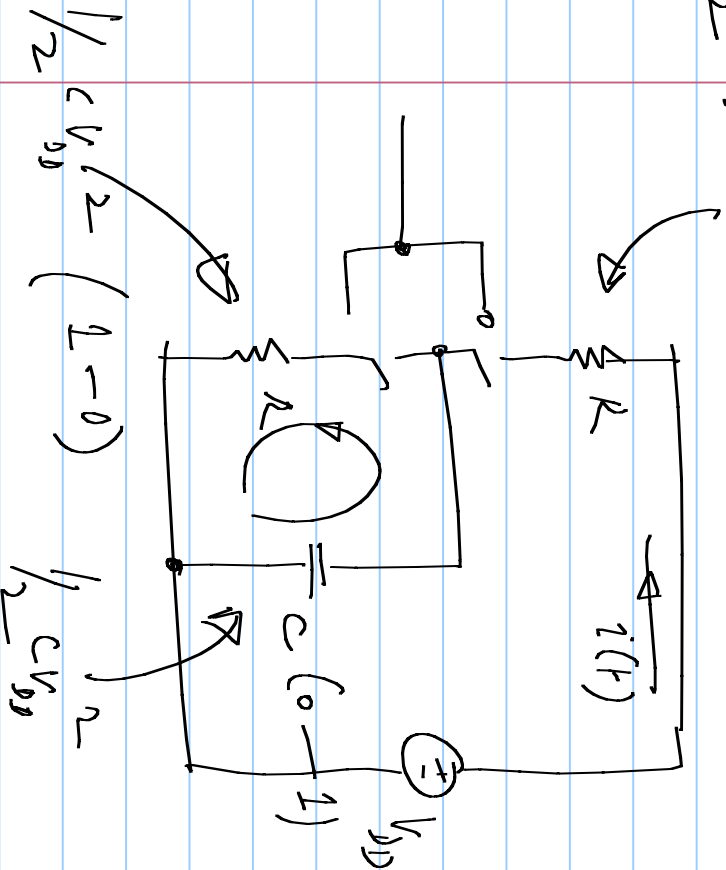


$$i = \frac{C \cdot dV_{out}}{dt}$$

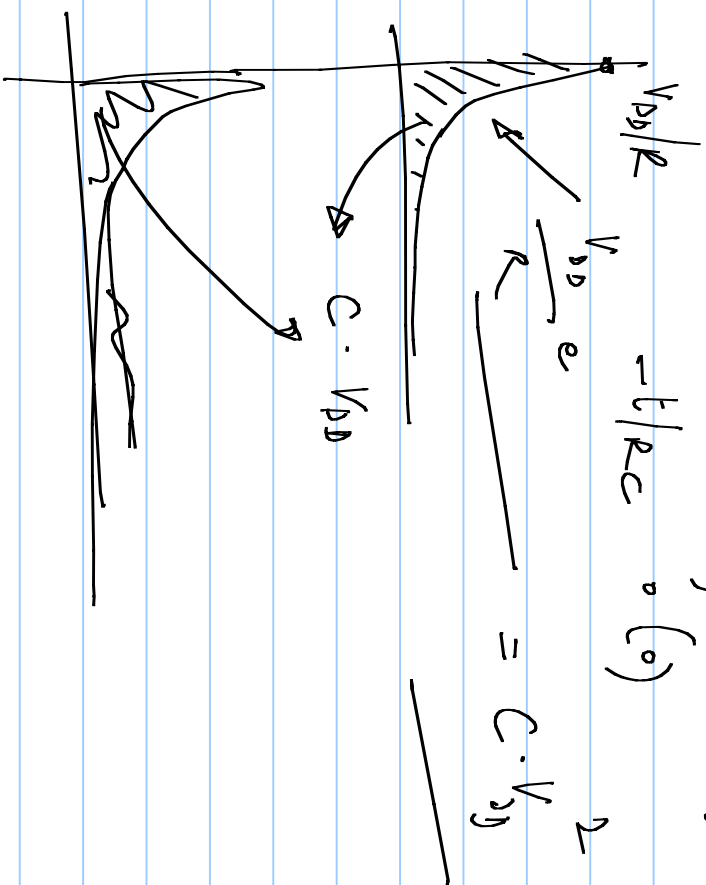
$$E = \int_{V_{DD}}^{\infty} C \cdot V_{DD} \cdot i(t) dt$$

$$P = \sqrt{C \cdot V_{DD}^2} \cdot f \quad (0 \rightarrow \infty) = \int_{V_{DD}}^{\infty} V_{DD} \cdot C \cdot \frac{dV_{out}}{dt} \cdot dt$$

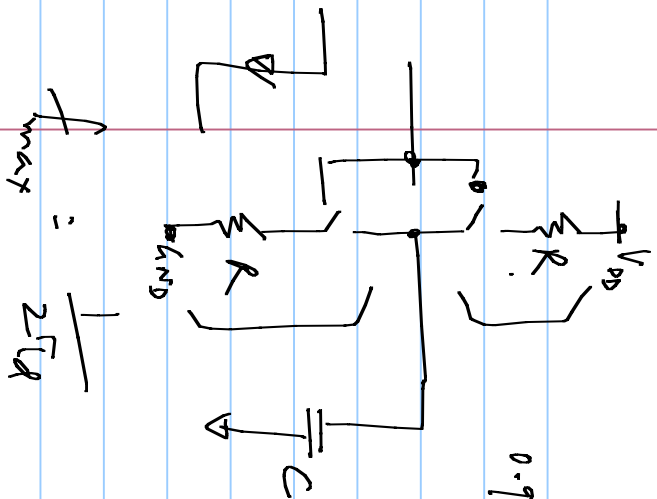
$$\frac{1}{2} C V_{DD}^2$$



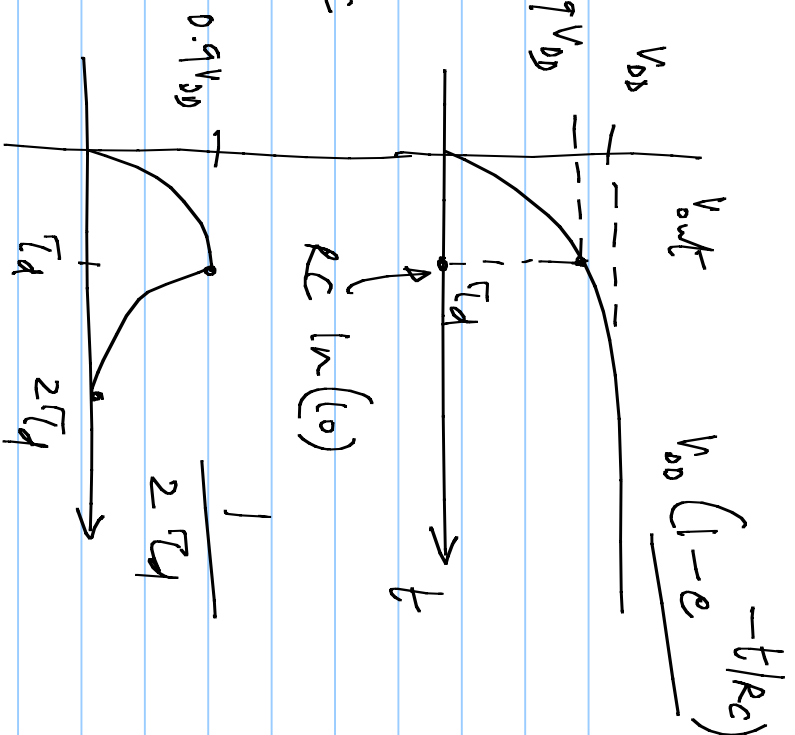
$$\frac{1}{2} C V_{DD}^2 (1-0)$$



$$P = C \cdot V_{DD}^2 \cdot f$$

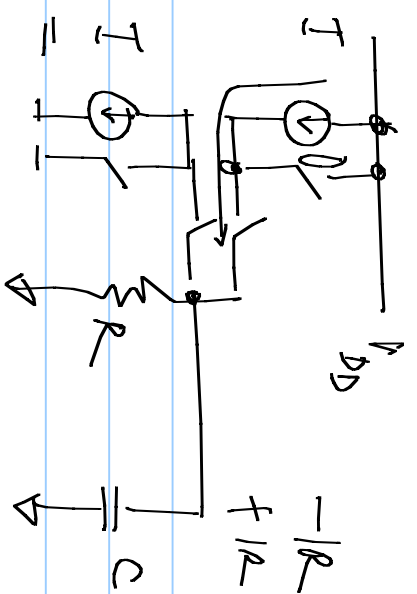


$$f_{max} = \frac{1}{2\tau_d}$$



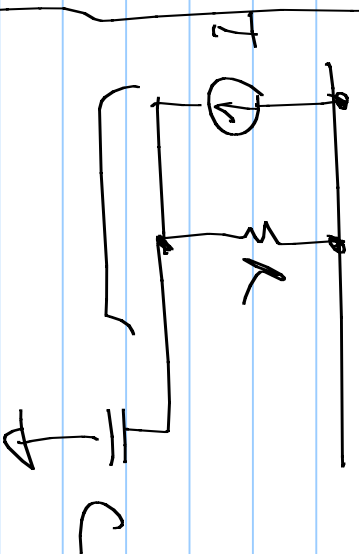
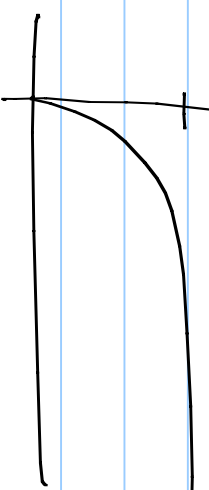
$$P = C \cdot V_{DD}^2 \cdot \frac{1}{2\tau_d}$$

$$P \cdot \tau_d = \frac{C \cdot V_{DD}^2}{2} = \frac{V_{DD}^2 (C \tau_d)}{2}$$



$$I \cdot V_{DD} \cdot \Delta t$$

$$I \cdot R (1 - e^{-t/RC})$$



$$V_{out} = (1 - 2e^{-t/RC}) \cdot IR$$

$$1 - 2e^{-t/RC} = 0.9$$

$$e^{-t/RC} = 0.05$$

Reduce IR

$$T_1 = RC \ln(20)$$

$$\underline{\underline{P \cdot T_1}} = 1 \cdot V_{DD} \cdot \frac{1}{2} \cdot RC \ln(20) = \frac{C \cdot V_{DD} (IR) \ln(20)}{2} \cdot \text{Current mode}$$

$$P \cdot T_1 = \frac{C \cdot V_{DD}^2}{2} \cdot \text{CMOS } P = \frac{C V_{DD}^2}{2 T_1} \cdot \text{logic}$$

— Noise margin is reduced [2 logic levels are closer]
 t_b each other

→ Static power - Same at LF & HF

→ More elaborate circuitry.